



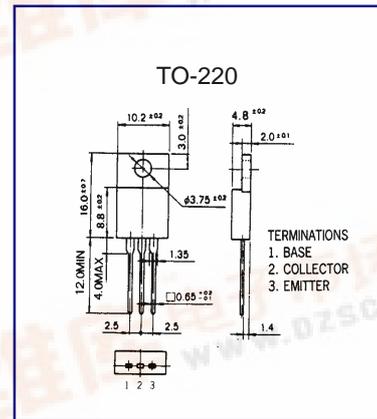
# 2SB595 PNP EPITAXIAL SILICON TRANSISTOR

## LOW FREQUENCY POWER AMPLIFIER

- Complement to 2SD525

### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	VCBO	-100	V
Collector-Emitter Voltage	VCEO	-100	V
Emitter-Base voltage	VEBO	-5	V
Collector Current (DC)	I <sub>C</sub>	-5	A
Collector Dissipation (T <sub>c</sub> =25°C)	P <sub>c</sub>	40	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-50~150	°C



### ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> = -100V, I <sub>E</sub> =0			-10	μA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> = -5V, I <sub>C</sub> =0			10	μA
DC Current Gain	h <sub>FE1</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> =-1A	40		320	
Collector- Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-4A, I <sub>B</sub> =-0.4A			-2.0	V
Current Gain Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> =-0.5A		8		MHz

